

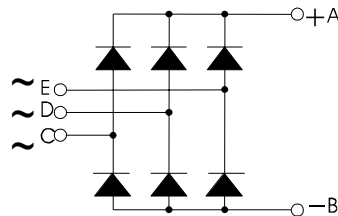
Three Phase Rectifier Bridges

PSD 162

I_{dAV} = 175 A
 V_{RRM} = 800-1800 V

Preliminary Data Sheet

V_{RSM} V	V_{RRM} V	Type
800	800	PSD 162/08
1200	1200	PSD 162/12
1400	1400	PSD 162/14
1600	1600	PSD 162/16
1800	1800	PSD 162/18



Symbol	Test Conditions			Maximum Ratings	
I_{dAV}	$T_C = 90^\circ\text{C}$, module			175	A
I_{FSM}	$T_{VJ} = 45^\circ\text{C}$	$t = 10\text{ ms}$	(50 Hz), sine	1800	A
	$V_R = 0$	$t = 8.3\text{ ms}$	(60 Hz), sine	1950	A
	$T_{VJ} = T_{VJM}$	$t = 10\text{ ms}$	(50 Hz), sine	1600	A
	$V_R = 0$	$t = 8.3\text{ ms}$	(60 Hz), sine	1800	A
$\int i^2 dt$	$T_{VJ} = 45^\circ\text{C}$	$t = 10\text{ ms}$	(50 Hz), sine	16200	$\text{A}^2\text{ s}$
	$V_R = 0$	$t = 8.3\text{ ms}$	(60 Hz), sine	16200	$\text{A}^2\text{ s}$
	$T_{VJ} = T_{VJM}$	$t = 10\text{ ms}$	(50 Hz), sine	12800	$\text{A}^2\text{ s}$
	$V_R = 0$	$t = 8.3\text{ ms}$	(60 Hz), sine	13400	$\text{A}^2\text{ s}$
T_{VJ}				-40 ... + 150	$^\circ\text{C}$
T_{VJM}				150	$^\circ\text{C}$
T_{stg}				-40 ... + 125	$^\circ\text{C}$
V_{ISOL}	50/60 HZ, RMS	$t = 1\text{ min}$		2500	V ~
	$I_{ISOL} \leq 1\text{ mA}$	$t = 1\text{ s}$		3000	V ~
M_d	Mounting torque	(M6)		5	Nm
	Terminal connection torque	(M6)		5	Nm
Weight	typ.			270	g

Features

- Package with screw terminals
- Isolation voltage 3000 V~
- Planar glasspassivated chips
- Blocking voltage up to 1800 V
- Low forward voltage drop
- UL registered E 148688

Applications

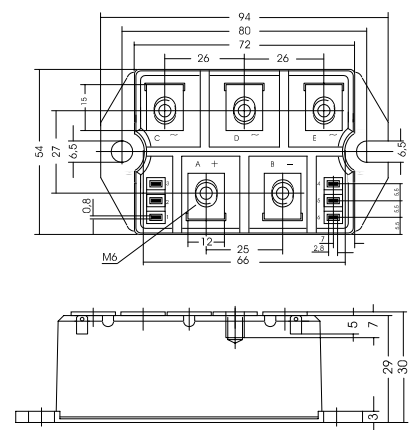
- Supplies for DC power equipment
- Input rectifiers for PWM inverter
- Battery DC power supplies
- Field supply for DC motors

Advantages

- Easy to mount with two screws
- Space and weight savings
- Improved temperature and power cycling capability

Package, style and outline

Dimensions in mm (1mm = 0.0394")



Symbol	Test Conditions			Characteristic Value	
I_R	$V_R = V_{RRM}$	$T_{VJ} = 25^\circ\text{C}$	$\leq$	0.3	mA
	$V_R = V_{RRM}$	$T_{VJ} = T_{VJM}$	$\leq$	5	mA
V_F	$I_F = 300\text{ A}$	$T_{VJ} = 25^\circ\text{C}$	$\leq$	1.55	V
V_{TO}	For power-loss calculations only			0.8	V
r_T	$T_{VJ} = T_{VJM}$			3	$\text{m}\Omega$
R_{thJC}	per diode; DC current			0.65	K/W
	per module			0.108	K/W
R_{thJK}	per diode; DC current			0.83	K/W
	per module			0.138	K/W
d_s	Creeping distance on surface			10.0	mm
d_A	Creeping distance in air			9.4	mm
a	Max. allowable acceleration			50	m/s^2

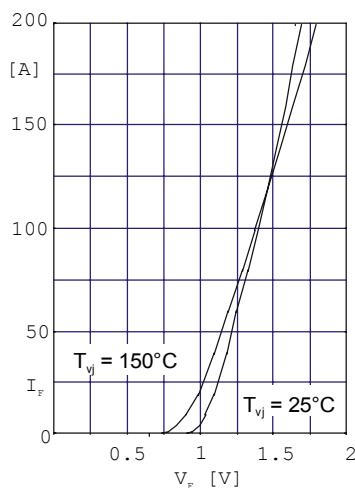


Fig. 1 Forward current versus voltage drop per diode

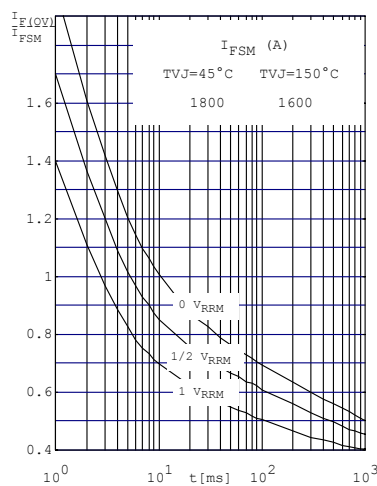


Fig. 2 Surge overload current per diode I_{FSM} : Crest value. t : duration

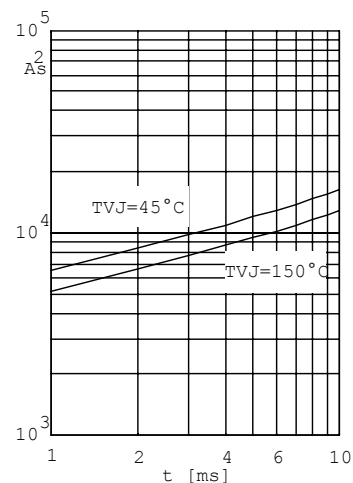


Fig. 3 $\int i^2 dt$ versus time (1-10ms) per diode (or thyristor)

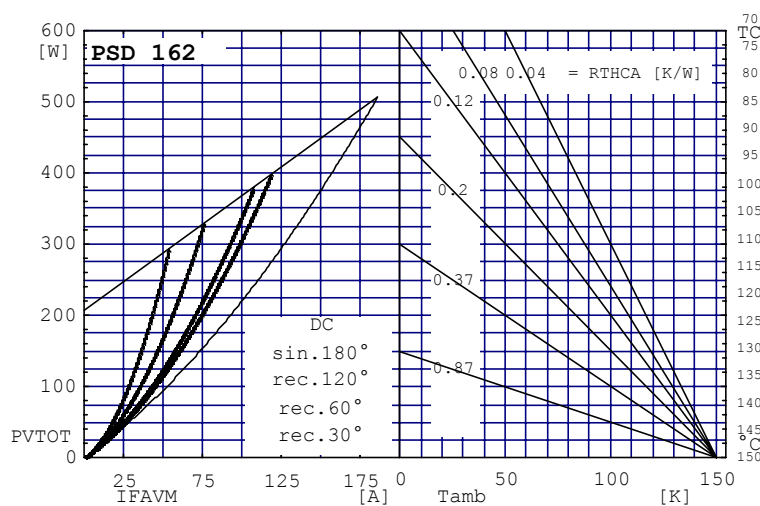


Fig. 4 Power dissipation versus direct output current and ambient temperature

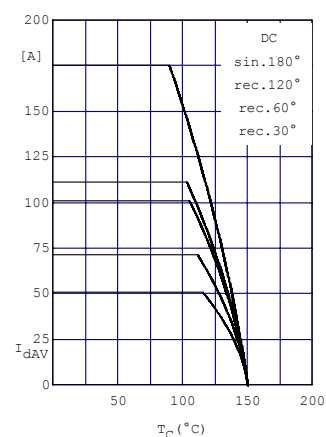


Fig. 5 Maximum forward current at case temperature

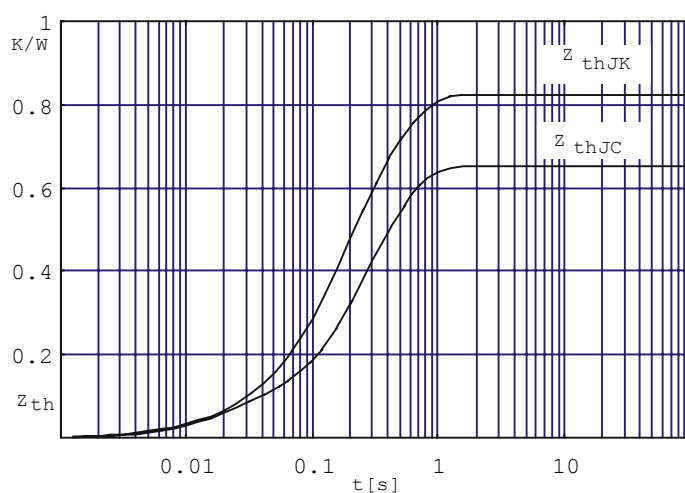


Fig. 6 Transient thermal impedance per diode (or thyristor), calculated